

MOSFET, Power; N-Ch; VDSS 55V; RDS(ON) 5.8Milliohms; ID 42A; D-Pak (TO-252AA); -55deg

Manufacturers	<a href="#">Infineon Technologies Corporation</a>
Package/Case	TO-252
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRFR1010ZPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

Specifically designed for Automotive applications, this MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications

## Features

Optimized for broadest availability from distribution partners

Product qualification according to JEDEC standard

Normal level : Optimized for 10 V gate drive voltage

Industry standard surface-mount power package

Capable of being wave-soldered

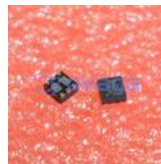


## Related Products



### [IRLTS6342TRPBF](#)

Infineon Technologies Corporation  
TSOP-6



### [IRLHS6376TRPBF](#)

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